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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	147
Number of Gates	199000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1k50qc208-3aa

For more information on the configuration of ACEX 1K devices, see the following documents:

- *Configuration Devices for ACEX, APEX, FLEX, & Mercury Devices Data Sheet*
- *MasterBlaster Serial/USB Communications Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *BitBlaster Serial Download Cable Data Sheet*

ACEX 1K devices are supported by Altera development systems, which are integrated packages that offer schematic, text (including AHDL), and waveform design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, and device configuration. The software provides EDIF 2 0 0 and 3 0 0, LPM, VHDL, Verilog HDL, and other interfaces for additional design entry and simulation support from other industry-standard PC- and UNIX workstation-based EDA tools.

The Altera software works easily with common gate array EDA tools for synthesis and simulation. For example, the Altera software can generate Verilog HDL files for simulation with tools such as Cadence Verilog-XL. Additionally, the Altera software contains EDA libraries that use device-specific features such as carry chains, which are used for fast counter and arithmetic functions. For instance, the Synopsys Design Compiler library supplied with the Altera development system includes DesignWare functions that are optimized for the ACEX 1K device architecture.

The Altera development systems run on Windows-based PCs and Sun SPARCstation, and HP 9000 Series 700/800 workstations.

For more information, see the *MAX+PLUS II Programmable Logic Development System & Software Data Sheet* and the *Quartus Programmable Logic Development System & Software Data Sheet*.

Functional Description

Each ACEX 1K device contains an enhanced embedded array that implements memory and specialized logic functions, and a logic array that implements general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 4,096 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in a single logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions, such as LPM functions, can take advantage of the EAB automatically.

The ACEX 1K enhanced EAB supports dual-port RAM. The dual-port structure is ideal for FIFO buffers with one or two clocks. The ACEX 1K EAB can also support up to 16-bit-wide RAM blocks. The ACEX 1K EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, allowing the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

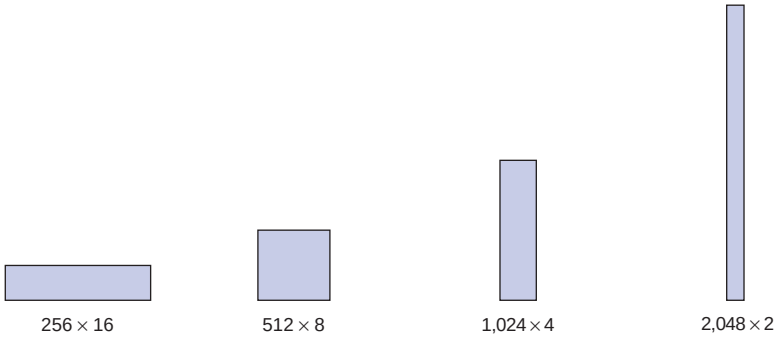
The EAB can also be used for bidirectional, dual-port memory applications where two ports read or write simultaneously. To implement this type of dual-port memory, two EABs are used to support two simultaneous reads or writes.

Alternatively, one clock and clock enable can be used to control the input registers of the EAB, while a different clock and clock enable control the output registers (see Figure 2).

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the write enable signal. In contrast, the EAB's synchronous RAM generates its own write enable signal and is self-timed with respect to the input or write clock. A circuit using the EAB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256 × 16; 512 × 8; 1,024 × 4; or 2,048 × 2. Figure 5 shows the ACEX 1K EAB memory configurations.

Figure 5. ACEX 1K EAB Memory Configurations



Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 16 RAM blocks can be combined to form a 256 × 32 block, and two 512 × 8 RAM blocks can be combined to form a 512 × 16 block. Figure 6 shows examples of multiple EAB combination.

Figure 6. Examples of Combining ACEX 1K EABs

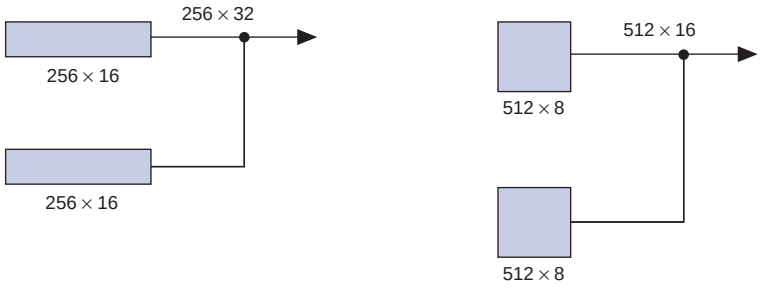
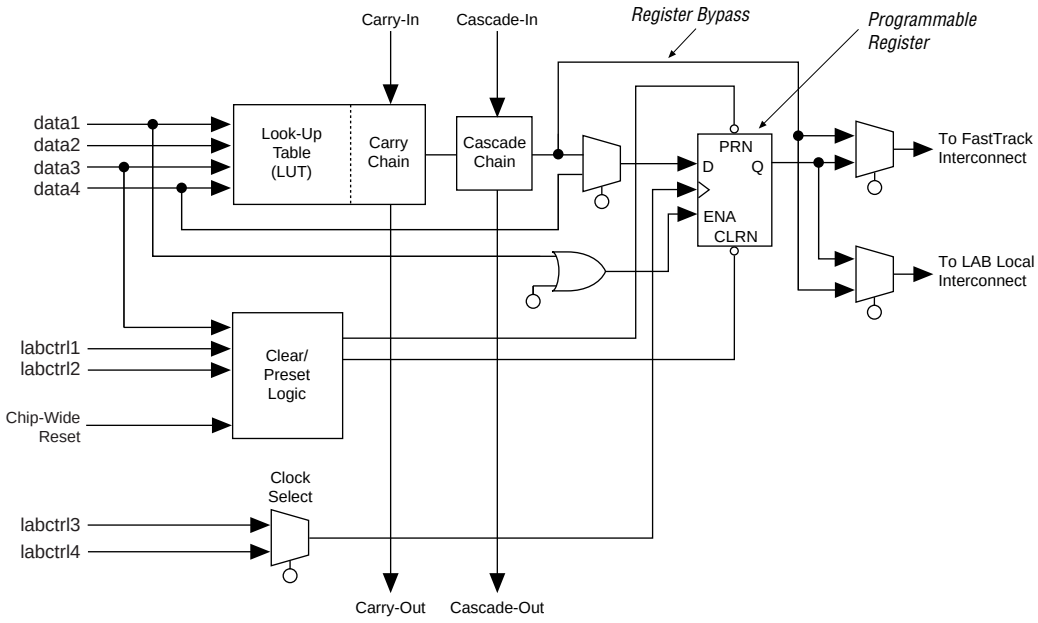


Figure 8. ACEX 1K Logic Element



The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the flipflop is bypassed and the LUT's output drives the LE's output.

The LE has two outputs that drive the interconnect: one drives the local interconnect, and the other drives either the row or column FastTrack Interconnect routing structure. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

The ACEX 1K architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders, and the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in a LAB and all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Asynchronous Clear

The flipflop can be cleared by either LABCTRL1 or LABCTRL2. In this mode, the preset signal is tied to VCC to deactivate it.

Asynchronous Preset

An asynchronous preset is implemented as an asynchronous load, or with an asynchronous clear. If DATA3 is tied to VCC, asserting LABCTRL1 asynchronously loads a one into the register. Alternatively, the Altera software can provide preset control by using the clear and inverting the register's input and output. Inversion control is available for the inputs to both LEs and IOEs. Therefore, if a register is preset by only one of the two LABCTRL signals, the DATA3 input is not needed and can be used for one of the LE operating modes.

Asynchronous Preset & Clear

When implementing asynchronous clear and preset, LABCTRL1 controls the preset, and LABCTRL2 controls the clear. DATA3 is tied to VCC, so that asserting LABCTRL1 asynchronously loads a one into the register, effectively presetting the register. Asserting LABCTRL2 clears the register.

Asynchronous Load with Clear

When implementing an asynchronous load in conjunction with the clear, LABCTRL1 implements the asynchronous load of DATA3 by controlling the register preset and clear. LABCTRL2 implements the clear by controlling the register clear; LABCTRL2 does not have to feed the preset circuits.

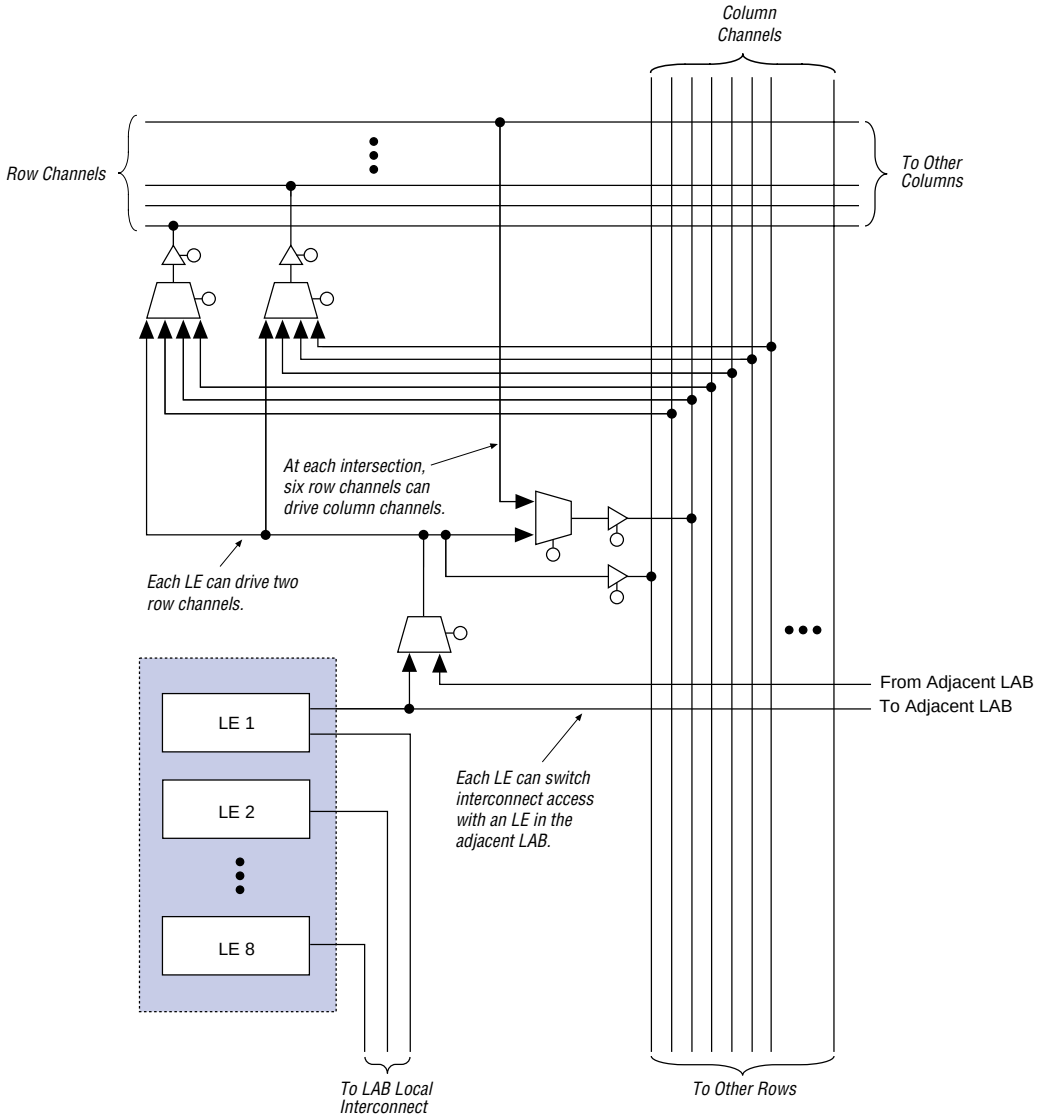
Asynchronous Load with Preset

When implementing an asynchronous load in conjunction with preset, the Altera software provides preset control by using the clear and inverting the input and output of the register. Asserting LABCTRL2 presets the register, while asserting LABCTRL1 loads the register. The Altera software inverts the signal that drives DATA3 to account for the inversion of the register's output.

Asynchronous Load without Preset or Clear

When implementing an asynchronous load without preset or clear, LABCTRL1 implements the asynchronous load of DATA3 by controlling the register preset and clear.

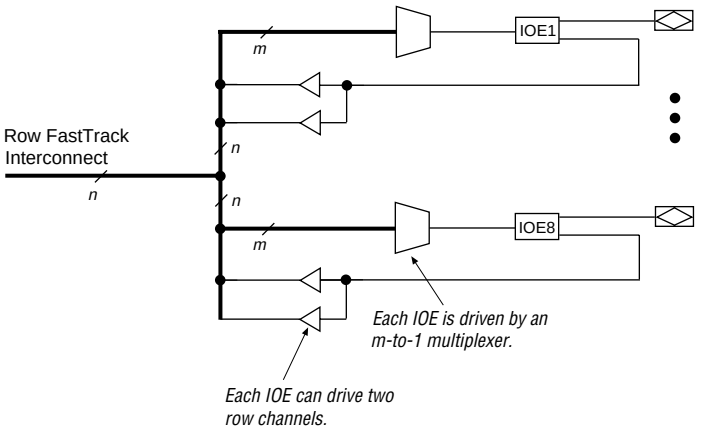
Figure 13. ACEX 1K LAB Connections to Row & Column Interconnect



Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel (see Figure 16).

Figure 16. ACEX 1K Row-to-IOE Connections *Note (1)*



Note:
(1) The values for *m* and *n* are shown in Table 8.

Table 8 lists the ACEX 1K row-to-IOE interconnect resources.

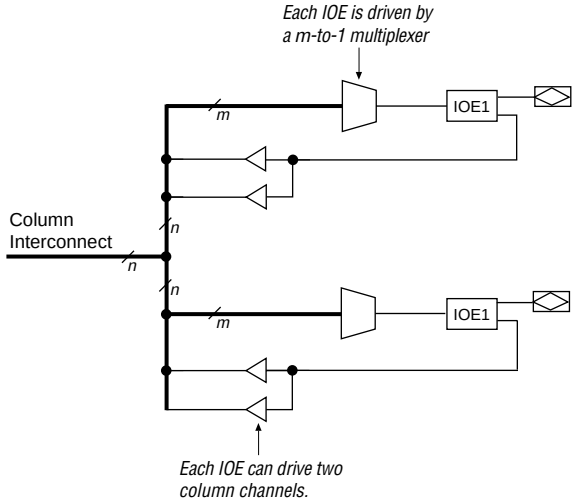
Table 8. ACEX 1K Row-to-IOE Interconnect Resources

Device	Channels per Row *(n)*	Row Channels per Pin *(m)*
EP1K10	144	18
EP1K30	216	27
EP1K50	216	27
EP1K100	312	39

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels is different for each IOE (see Figure 17).

Figure 17. ACEX 1K Column-to-IOE Connections *Note (1)*



Note:
(1) The values for *m* and *n* are shown in Table 9.

Table 9 lists the ACEX 1K column-to-IOE interconnect resources.

Table 9. ACEX 1K Column-to-IOE Interconnect Resources

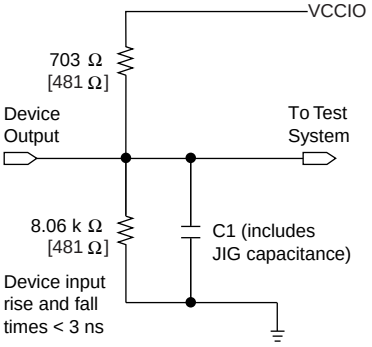
Device	Channels per Column *(n)*	Column Channels per Pin *(m)*
EP1K10	24	16
EP1K30	24	16
EP1K50	24	16
EP1K100	24	16

Generic Testing

Each ACEX 1K device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for ACEX 1K devices are made under conditions equivalent to those shown in Figure 21. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 21. ACEX 1K AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers in brackets are for 2.5-V devices or outputs. Numbers without brackets are for 3.3-V devices or outputs.



Operating Conditions

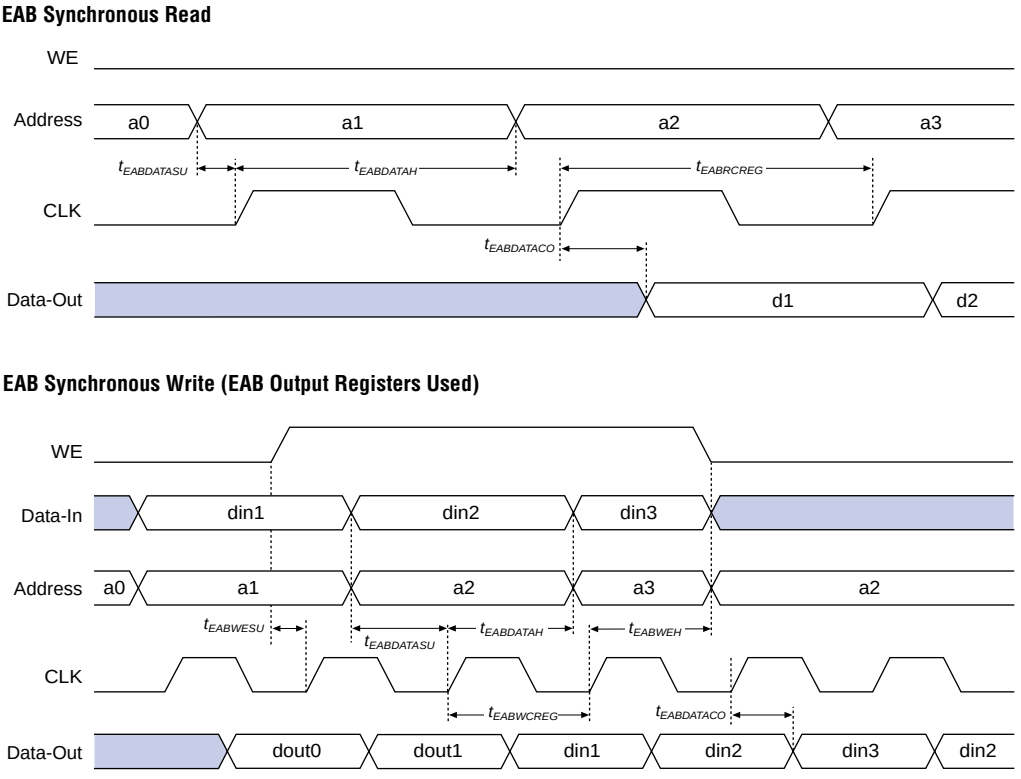
Tables 18 through 21 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V ACEX 1K devices.

Table 18. ACEX 1K Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, TQFP, and BGA packages, under bias		135	° C

Table 20. ACEX 1K Device DC Operating Conditions (Part 2 of 2) *Notes (6), (7)*						
Symbol	**Parameter**	**Conditions**	**Min**	**Typ**	**Max**	**Unit**
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(10)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(10)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(10)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.375 V *(10)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.375 V *(10)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.375 V *(10)*			0.7	V
I_I	Input pin leakage current	V_I = 5.3 to –0.3 V *(11)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.3 to –0.3 V *(11)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load, no toggling inputs		5		mA
		V_I = ground, no load, no toggling inputs *(12)*		10		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(13)*	30		80	kΩ

Figure 30. EAB Synchronous Timing Waveforms



Tables 22 through 26 describe the ACEX 1K device internal timing parameters.

Table 22. LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	Conditions
t_{LUT}	LUT delay for data-in	
t_{CLUT}	LUT delay for carry-in	
t_{RLUT}	LUT delay for LE register feedback	
t_{PACKED}	Data-in to packed register delay	
t_{EN}	LE register enable delay	
t_{CICO}	Carry-in to carry-out delay	
t_{CGEN}	Data-in to carry-out delay	
t_{CGENR}	LE register feedback to carry-out delay	

Table 22. LE Timing Microparameters (Part 2 of 2) *Note (1)*		
Symbol	**Parameter**	**Conditions**
t_{CASC}	Cascade-in to cascade-out delay	
t_{C}	LE register control signal delay	
t_{CO}	LE register clock-to-output delay	
t_{COMB}	Combinatorial delay	
t_{SU}	LE register setup time for data and enable signals before clock; LE register recovery time after asynchronous clear, preset, or load	
t_{H}	LE register hold time for data and enable signals after clock	
t_{PRE}	LE register preset delay	
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 23. IOE Timing Microparameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 25. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 37. EP1K30 Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t_{COMB}		0.4		0.4		0.6	ns
t_{SU}	0.4		0.6		0.6		ns
t_{H}	0.7		1.0		1.3		ns
t_{PRE}		0.8		0.9		1.2	ns
t_{CLR}		0.8		0.9		1.2	ns
t_{CH}	2.0		2.5		2.5		ns
t_{CL}	2.0		2.5		2.5		ns

Table 38. EP1K30 Device IOE Timing Microparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.4		2.8		3.8	ns
t_{IOC}		0.3		0.4		0.5	ns
t_{IOCO}		1.0		1.1		1.6	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	1.2		1.4		1.9		ns
t_{IOH}	0.3		0.4		0.5		ns
t_{IOCLR}		1.0		1.1		1.6	ns
t_{OD1}		1.9		2.3		3.0	ns
t_{OD2}		1.4		1.8		2.5	ns
t_{OD3}		4.4		5.2		7.0	ns
t_{XZ}		2.7		3.1		4.3	ns
t_{ZX1}		2.7		3.1		4.3	ns
t_{ZX2}		2.2		2.6		3.8	ns
t_{ZX3}		5.2		6.0		8.3	ns
t_{INREG}		3.4		4.1		5.5	ns
t_{IOFD}		0.8		1.3		2.4	ns
t_{INCOMB}		0.8		1.3		2.4	ns

Table 43. EP1K30 External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (3)	2.8		3.9		5.2		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (4)	3.8		4.9		–		ns
$t_{INHBIDIR}$ (4)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
$t_{XZBIDIR}$ (3)		6.1		7.5		9.7	ns
$t_{ZXBIDIR}$ (3)		6.1		7.5		9.7	ns
$t_{OUTCOBIDIR}$ (4)	0.5	3.9	0.5	4.9	–	–	ns
$t_{XZBIDIR}$ (4)		5.1		6.5		–	ns
$t_{ZXBIDIR}$ (4)		5.1		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 22 through 29 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 44 through 50 show EP1K50 device external timing parameters.

Table 44. EP1K50 Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.8		1.1	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.6		0.7		0.9	ns
t_{PACKED}		0.2		0.3		0.4	ns
t_{EN}		0.6		0.7		0.9	ns
t_{CICO}		0.1		0.1		0.1	ns
t_{CGEN}		0.4		0.5		0.6	ns
t_{CGENR}		0.1		0.1		0.1	ns
t_{CASC}		0.5		0.8		1.0	ns
t_{C}		0.5		0.6		0.8	ns

Table 44. EP1K50 Device LE Timing Microparameters (Part 2 of 2) Note (1)							
Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t_{CO}		0.6		0.6		0.7	ns
t_{COMB}		0.3		0.4		0.5	ns
t_{SU}	0.5		0.6		0.7		ns
t_{H}	0.5		0.6		0.8		ns
t_{PRE}		0.4		0.5		0.7	ns
t_{CLR}		0.8		1.0		1.2	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 45. EP1K50 Device IOE Timing Microparameters Note (1)							
Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.3		1.3		1.9	ns
t_{IOC}		0.3		0.4		0.4	ns
t_{IOCO}		1.7		2.1		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.4		0.5		0.6		ns
t_{IOCLR}		0.2		0.2		0.4	ns
t_{OD1}		1.2		1.2		1.9	ns
t_{OD2}		0.7		0.8		1.7	ns
t_{OD3}		2.7		3.0		4.3	ns
t_{XZ}		4.7		5.7		7.5	ns
t_{ZX1}		4.7		5.7		7.5	ns
t_{ZX2}		4.2		5.3		7.3	ns
t_{ZX3}		6.2		7.5		9.9	ns
t_{INREG}		3.5		4.2		5.6	ns
t_{IOFD}		1.1		1.3		1.8	ns
t_{INCOMB}		1.1		1.3		1.8	ns

Table 46. EP1K50 Device EAB Internal Microparameters *Note (1)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.4		3.2	ns
$t_{EABDATA2}$		0.4		0.6		0.8	ns
t_{EABWE1}		1.0		1.4		1.9	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0.0		0.0		0.0	
t_{EABRE2}		0.4		0.6		0.8	
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		1.1		1.5	ns
$t_{EABBYPASS}$		0.0		0.0		0.0	ns
t_{EABSU}	0.7		1.0		1.3		ns
t_{EABH}	0.4		0.6		0.8		ns
t_{EABCLR}	0.8		1.1		1.5		
t_{AA}		2.0		2.8		3.8	ns
t_{WP}	2.0		2.8		3.8		ns
t_{RP}	1.0		1.4		1.9		
t_{WDSU}	0.5		0.7		0.9		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	1.0		1.4		1.9		ns
t_{WAH}	1.5		2.1		2.9		ns
t_{RASU}	1.5		2.1		2.8		
t_{RAH}	0.1		0.1		0.2		
t_{WO}		2.1		2.9		4.0	ns
t_{DD}		2.1		2.9		4.0	ns
t_{EABOUT}		0.0		0.0		0.0	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	1.5		2.0		2.5		ns

Table 53. EP1K100 Device EAB Internal Microparameters *Note (1)*							
Symbol	**Speed Grade**						**Unit**
	-1		**-2**		**-3**		
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.5		2.0		2.6	ns
$t_{EABDATA1}$		0.0		0.0		0.0	ns
t_{EABWE1}		1.5		2.0		2.6	ns
t_{EABWE2}		0.3		0.4		0.5	ns
t_{EABRE1}		0.3		0.4		0.5	ns
t_{EABRE2}		0.0		0.0		0.0	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.4		0.5	ns
$t_{EABBYPASS}$		0.1		0.1		0.2	ns
t_{EABSU}	0.8		1.0		1.4		ns
t_{EABH}	0.1		0.1		0.2		ns
t_{EABCLR}	0.3		0.4		0.5		ns
t_{AA}		4.0		5.1		6.6	ns
t_{WP}	2.7		3.5		4.7		ns
t_{RP}	1.0		1.3		1.7		ns
t_{WDSU}	1.0		1.3		1.7		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	1.6		2.1		2.8		ns
t_{WAH}	1.6		2.1		2.8		ns
t_{RASU}	3.0		3.9		5.2		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		1.5		2.0		2.6	ns
t_{DD}		1.5		2.0		2.6	ns
t_{EABOUT}		0.2		0.3		0.3	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.7		3.5		4.7		ns

Table 57. EP1K100 External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	Speed Grade						Unit
	-1		-2		-3		
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (3)	1.7		2.5		3.3		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (4)	2.0		2.8		–		ns
$t_{INHBIDIR}$ (4)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (3)	2.0	5.2	2.0	6.9	2.0	9.1	ns
$t_{XZBIDIR}$ (3)		5.6		7.5		10.1	ns
$t_{ZXBIDIR}$ (3)		5.6		7.5		10.1	ns
$t_{OUTCOBIDIR}$ (4)	0.5	3.0	0.5	4.6	–	–	ns
$t_{XZBIDIR}$ (4)		4.6		6.5		–	ns
$t_{ZXBIDIR}$ (4)		4.6		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 22 through 29 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Power Consumption

The supply power (P) for ACEX 1K devices can be calculated with the following equation:

$$P = P_{INT} + P_{IO} = (I_{CCSTANDBY} + I_{CCACTIVE}) \times V_{CC} + P_{IO}$$

The $I_{CCACTIVE}$ value depends on the switching frequency and the application logic. This value is calculated based on the amount of current that each LE typically consumes. The P_{IO} value, which depends on the device output load characteristics and switching frequency, can be calculated using the guidelines given in *Application Note 74 (Evaluating Power for Altera Devices).*

Compared to the rest of the device, the embedded array consumes a negligible amount of power. Therefore, the embedded array can be ignored when calculating supply current.

Revision History

The information contained in the *ACEX 1K Programmable Logic Device Family Data Sheet* version 3.4 supersedes information published in previous versions.

The following changes were made to the *ACEX 1K Programmable Logic Device Family Data Sheet* version 3.4: added extended temperature support.